

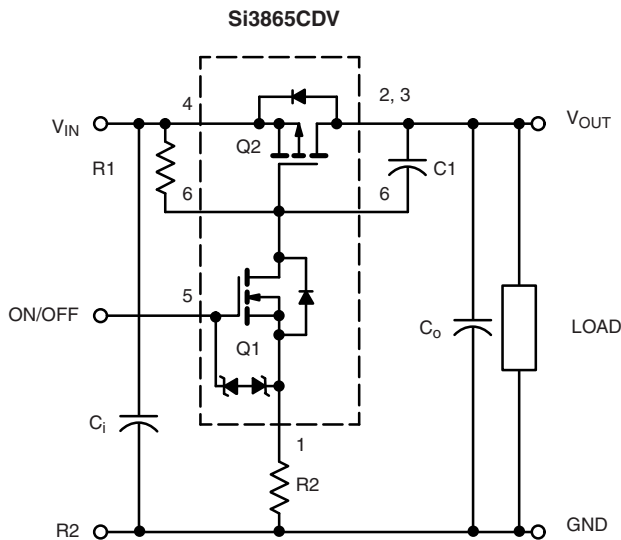
Load Switch with Level-Shift

PRODUCT SUMMARY		
V_{DS2} (V) (V_{IN})	$R_{DS(on)}$ (Ω)	I_D (A)
1.8 to 12	0.060 at $V_{IN} = 4.5$ V	2.8
	0.095 at $V_{IN} = 2.5$ V	2.2
	0.130 at $V_{IN} = 1.8$ V	1.9

DESCRIPTION

The Si3865CDV includes a P- and N-Channel MOSFET in a single TSOP-6 package. The low on-resistance P-Channel TrenchFET is tailored for use as a load switch. The N-Channel, with an external resistor, can be used as a level-

APPLICATION CIRCUITS



COMPONENTS		
R1	Pull-Up Resistor	Typical 10 k Ω to 1 M Ω *
R2	Optional Slew-Rate Control	Typical 0 to 100 k Ω *
C1	Optional Slew-Rate Control	Typical 1000 pF

Note:

* Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on at 1.8 V input.

FEATURES

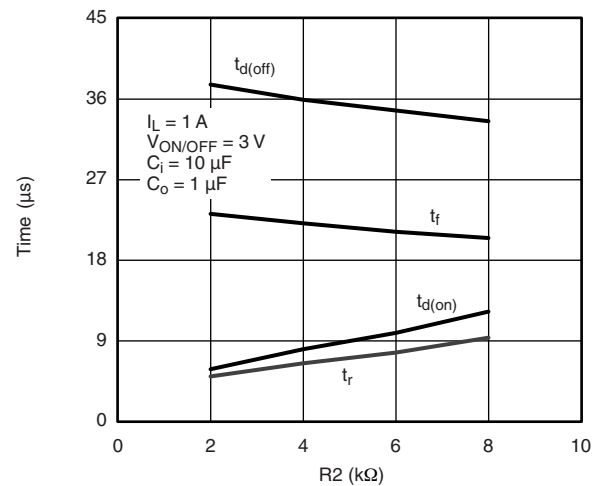
- Halogen-free According to IEC 61249-2-21 Definition
- 60 m Ω Low $R_{DS(on)}$ TrenchFET[®]
- 1.8 V to 12 V Input
- 1.5 V to 8 V Logic Level Control
- Low Profile, Small Footprint TSOP-6 Package
- 3000 V ESD Protection On Input Switch, $V_{ON/OFF}$
- Adjustable Slew-Rate
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Load Switching for Portable Devices

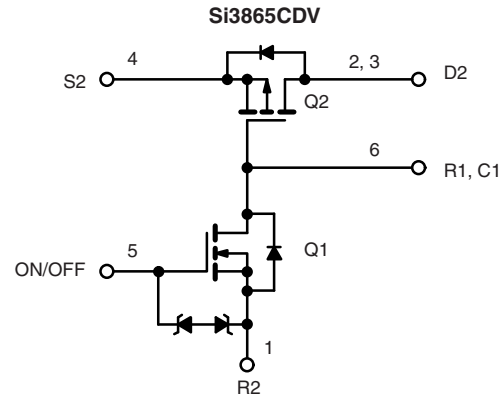
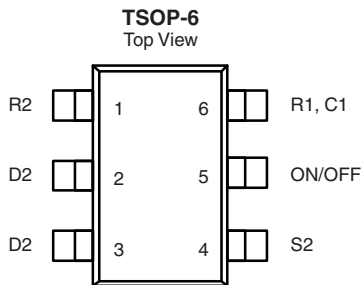
shift to drive the P-Channel load-switch. The N-Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si3865CDV operates on supply lines from 1.8 to 12 V, and can drive loads up to 2.8 A.



Switching Variation
R2 at $V_{IN} = 2.5$ V, R1 = 20 k Ω

The Si3865CDV is ideally suited for high-side load switching in portable applications. The integrated N-Channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

FUNCTIONAL BLOCK DIAGRAM



Ordering Information: Si3865CDV-T1-E3 (Lead (Pb)-free)
Si3865CDV-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Input Voltage	V_{IN} (V_{DS2})	12	V	
Gate-Source Voltage	V_{GS2}	8		
ON/OFF Voltage	$V_{ON/OFF}$ (V_{GS1})	8		
Load Current	Continuous ^{a, b}	I_L	± 2.8	A
	Pulsed ^{b, c}		± 6	
Continuous Intrinsic Diode Conduction ^a	I_S	- 1		
Maximum Power Dissipation ^a	P_D	0.83	W	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$	
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)	ESD	3	kV	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (continuous current) ^a	R_{thJA}	130	150	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Foot (Q2)	R_{thJF}	75	90	

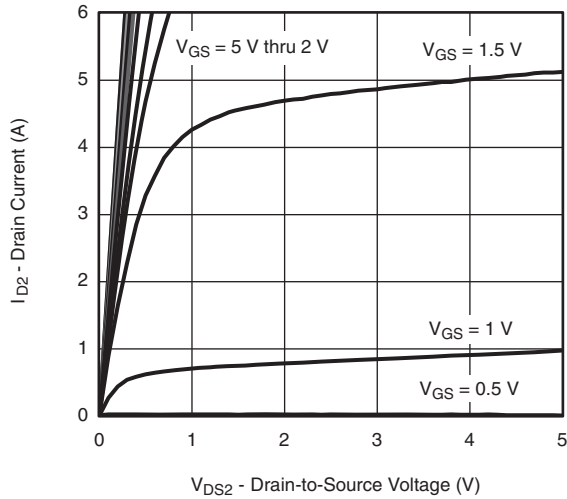
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF Characteristics						
Reverse Leakage Current	I_{FL}	$V_{IN} = 12\text{ V}, V_{ON/OFF} = 0\text{ V}$			1	μA
Diode Forward Voltage	V_{SD}	$I_S = -1\text{ A}$		- 0.77	- 1	V
ON Characteristics						
Input Voltage Range	V_{IN} (V_{DS2})		1.8		12	V
On-Resistance (P-Channel) at 1 A	$R_{DS(on)}$	$V_{ON/OFF} = 1.5\text{ V}, I_D = 1\text{ A}$	$V_{IN} = 4.5\text{ V}$	0.050	0.060	Ω
			$V_{IN} = 2.5\text{ V}$	0.073	0.095	
			$V_{IN} = 1.8\text{ V}$	0.100	0.130	
On-State (P-Channel) Drain-Current	$I_{D(on)}$	$V_{IN-OUT} \leq 0.2\text{ V}, V_{IN} = 5\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1			A
		$V_{IN-OUT} \leq 0.3\text{ V}, V_{IN} = 3\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1			

Notes:

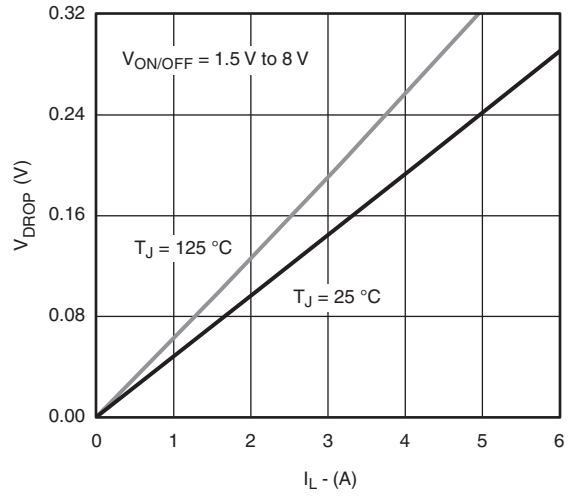
- a. Surface Mounted on FR4 board.
- b. $V_{IN} = 8\text{ V}, V_{ON/OFF} = 8\text{ V}, T_A = 25\text{ }^\circ\text{C}$.
- c. Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

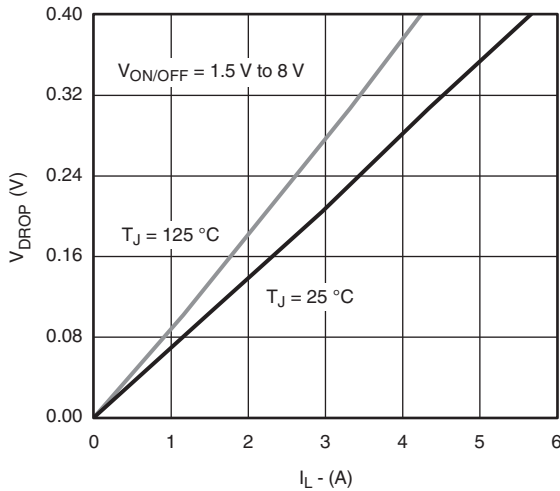
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



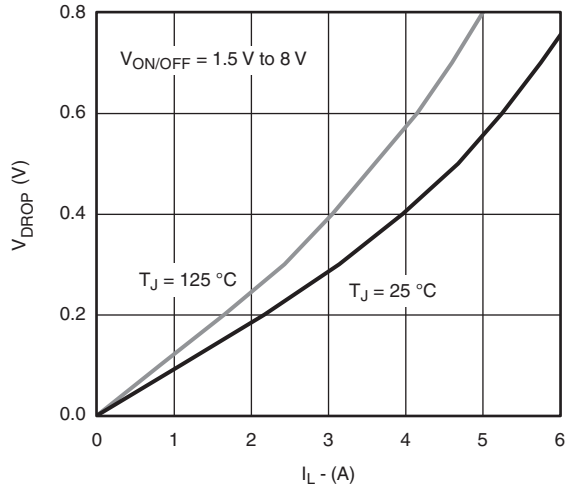
Output Characteristics



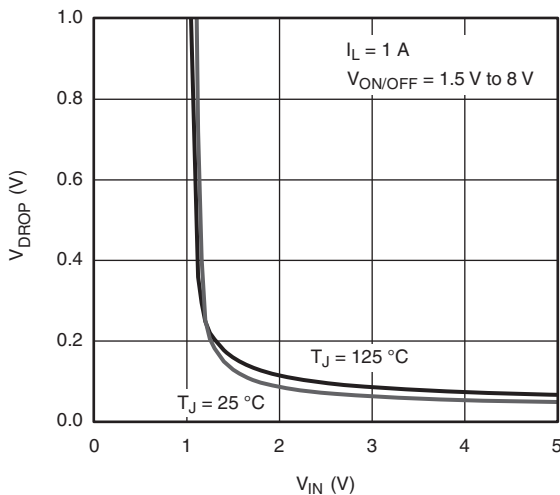
V_{DROP} vs. I_L at $V_{IN} = 4.5$ V



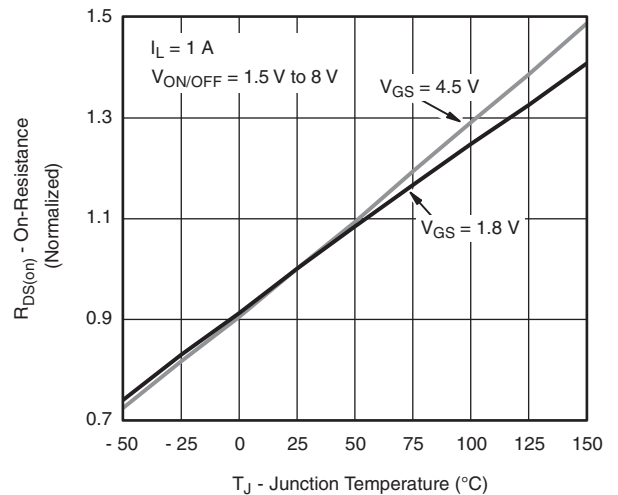
V_{DROP} vs. I_L at $V_{IN} = 2.5$ V



V_{DROP} vs. I_L at $V_{IN} = 1.8$ V

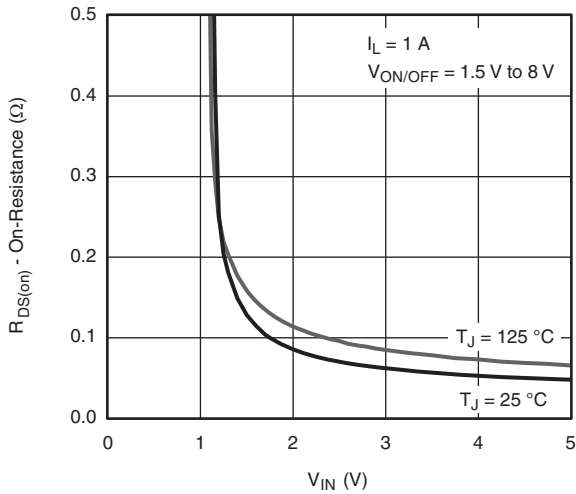


V_{DROP} vs. V_{IN} at $I_L = 1$ A

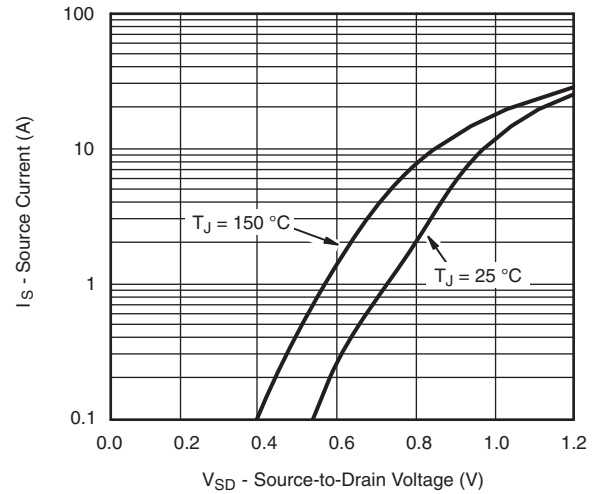


Normalized On-Resistance vs. Junction Temperature

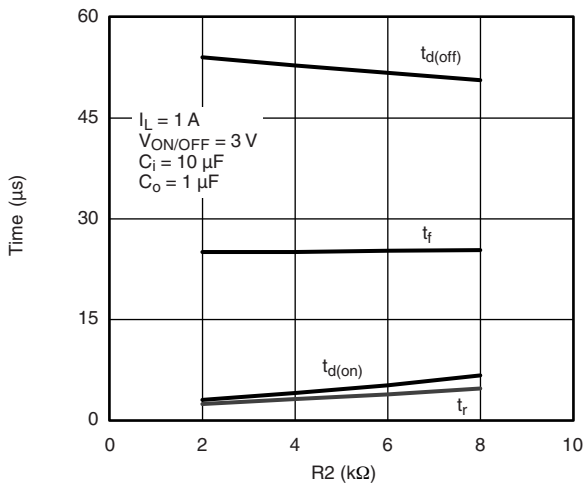
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



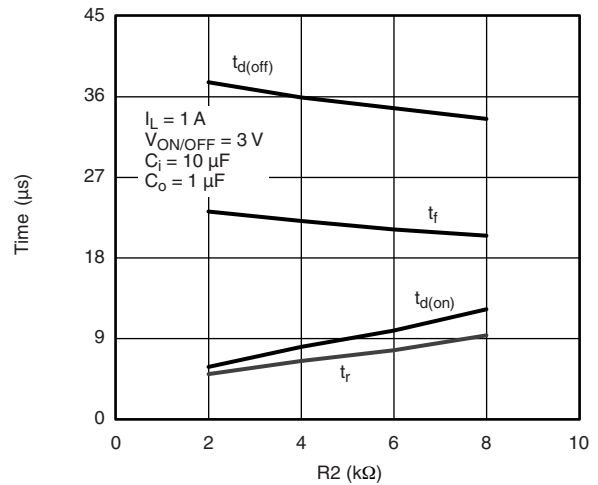
On-Resistance vs. Input Voltage



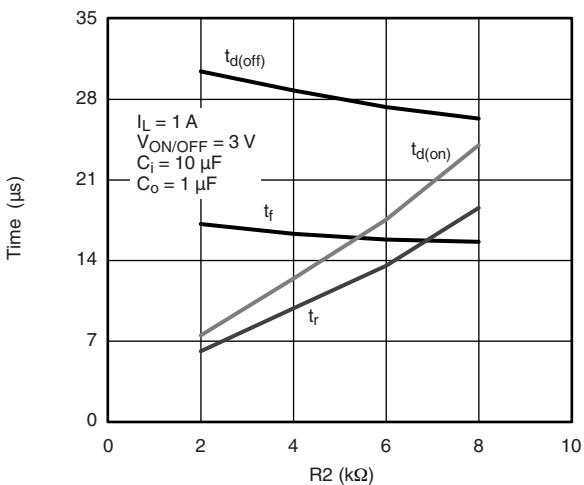
Source-Drain Diode Forward Voltage



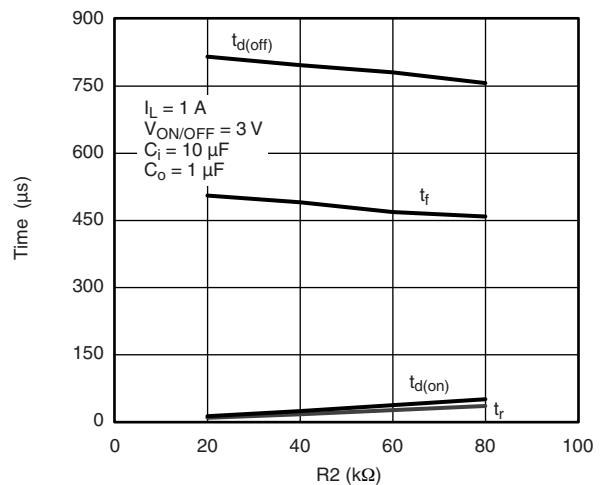
**Switching Variation
R2 at $V_{IN} = 4.5\text{ V}$, $R_1 = 20\ \text{k}\Omega$**



**Switching Variation
R2 at $V_{IN} = 2.5\text{ V}$, $R_1 = 20\ \text{k}\Omega$**

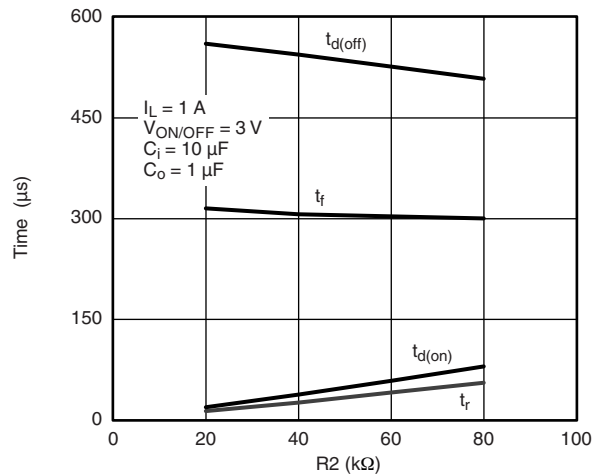


**Switching Variation
R2 at $V_{IN} = 1.8\text{ V}$, $R_1 = 20\ \text{k}\Omega$**

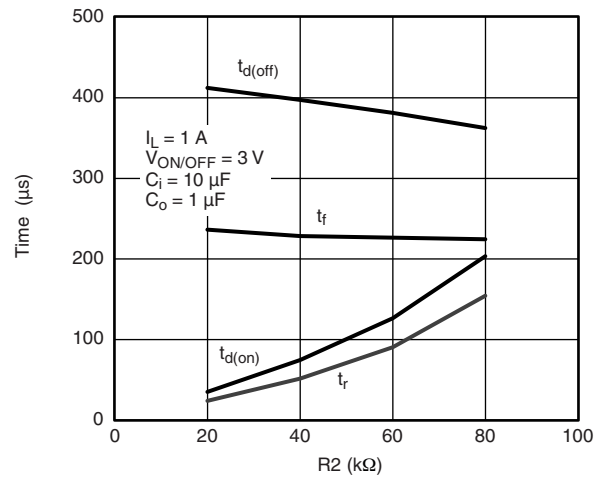


**Switching Variation
R2 at $V_{IN} = 4.5\text{ V}$, $R_1 = 300\ \text{k}\Omega$**

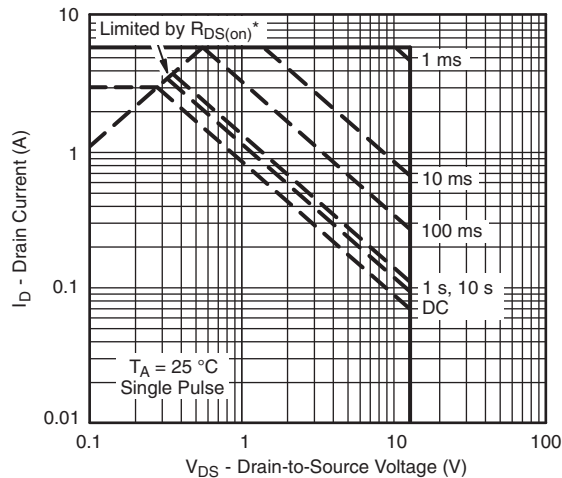
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



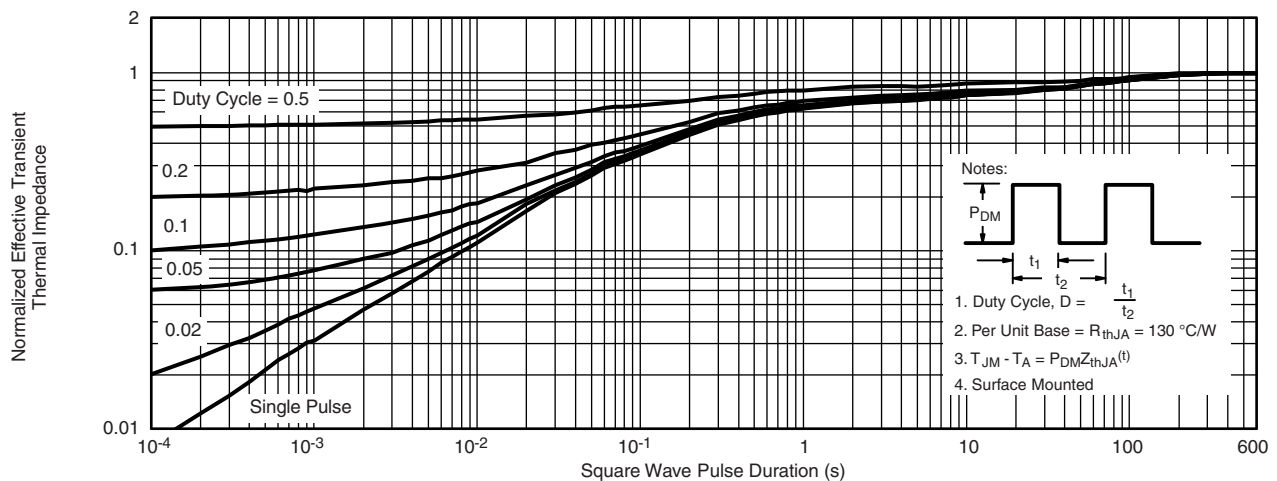
Switching Variation
R2 at $V_{IN} = 2.5 \text{ V}$, $R1 = 300 \text{ k}\Omega$



Switching Variation
R2 at $V_{IN} = 1.8 \text{ V}$, $R1 = 300 \text{ k}\Omega$



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Foot



Normalized Thermal Transient Impedance, Junction-to-Ambient

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TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C



5-LEAD TSOP



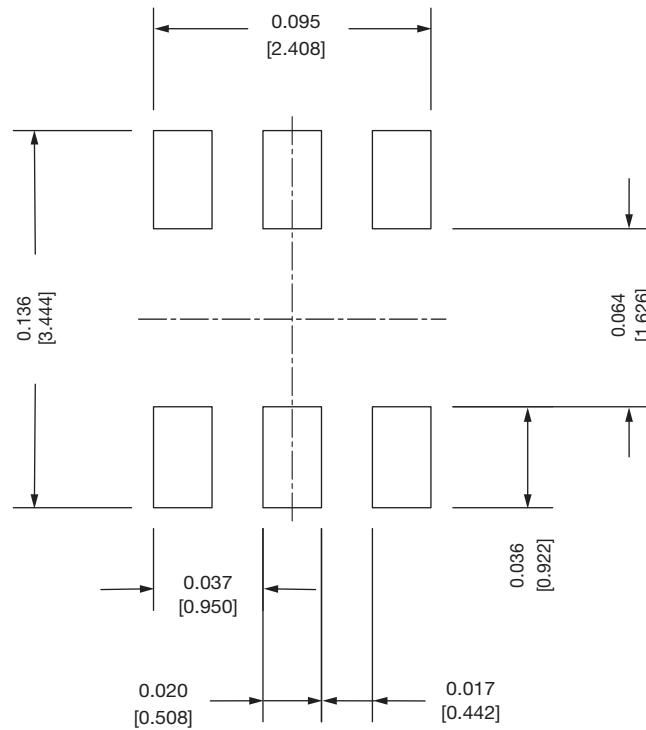
6-LEAD TSOP



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A₁	0.01	-	0.10	0.0004	-	0.004
A₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L₁	0.60 Ref			0.024 Ref		
L₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						



Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022
DWG: 3010



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